

Title (en)

EPITAXIAL SOLID-STATE SEMICONDUCTING HETERO-STRUCTURES AND METHOD FOR MAKING SAME

Title (de)

EPITAKTISCHE HALBLEITENDE FESTKÖRPER-HETEROSTRUKTUREN UND VERFAHREN ZU IHRER HERSTELLUNG

Title (fr)

HÉTÉROSTRUCTURES SEMI-CONDUCTRICES MONOLITHIQUES ÉPITAXIÉES ET LEUR PROCÉDÉ DE FABRICATION

Publication

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Application

EP 08837575 A 20080917

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Abstract (en)

[origin: WO2009047448A1] The invention mainly relates to a method for producing a solid-state semiconducting structure that comprises the steps of: (i) providing a monocrystalline substrate; (ii) epitaxially growing a layer of a monocrystalline oxide on said substrate; (iii) forming a sub-layer via the steps comprising: (a) removing the impurities from the surface of the monocrystalline oxide layer; (b) depositing by slow epitaxial growth a semiconducting sub-layer; and (iv) forming by epitaxial growth a monocrystalline semiconducting layer on the sub-layer thus formed. The invention also relates to solid-state semiconducting hetero-structures thus obtained.

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